

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	3437	(threshold near5 volt\$3) same (implant\$3 dpo\$3) same (nondopant non-dopant(heavy near5 atom) helium argon zenon Ze germanium Ge indium In)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 12:09
L7	3091	6 and oxide	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 09:37
L8	2972	7 and (source drain)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 11:50
L9	2940	8 and gate	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 09:37
L12	199	(threshold near5 volt\$3) same (implant\$3 dpo\$3) same (nondopant non-dopant(heavy near5 atom) helium argon zenon Xe germanium Ge indium In)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/06 11:52
L13	117	12 and (source drain)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/06 11:50
L14	38870	(threshold near5 volt\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/06 12:10
L15	361	14 and (APT (anti near3 puch near3 through) (punch near3 through) (anti near5 diffusion))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/06 12:10
L16	100361	(threshold near5 volt\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 12:10
L17	4837	16 and (APT (anti near3 puch near3 through) (punch near3 through) (anti near5 diffusion))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 12:10
L18	674	17 and (STI (shallow near5 trench))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/06 12:11